

N-Channel 60-V (D-S) MOSFET

Key Features:

- Low $r_{DS(on)}$ trench technology
- Low thermal impedance
- Fast switching speed

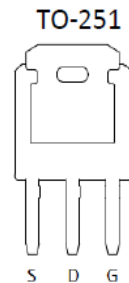
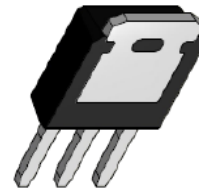
Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (m Ω)	I_D (A)
60	94 @ $V_{GS} = 10V$	19
	109 @ $V_{GS} = 4.5V$	18



RoHS
COMPLIANT
HALOGEN
FREE



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ^a	$T_A = 25^\circ\text{C}$	I_D	19	A
Pulsed Drain Current ^b		I_{DM}	75	
Continuous Source Current (Diode Conduction) ^a		I_S	42	A
Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	50	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	40	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Case	$R_{\theta JC}$	3	

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

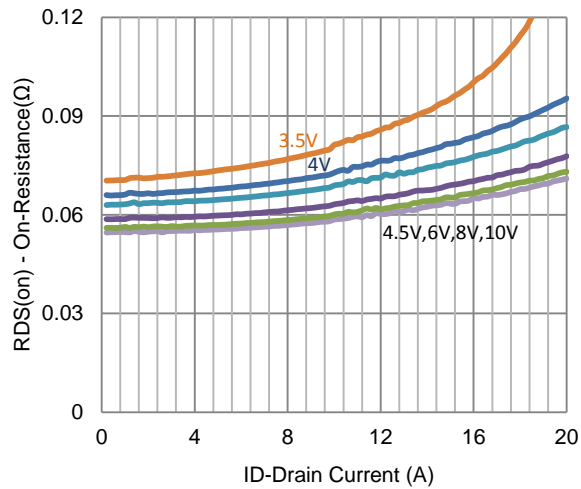
Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 48 V, V_{GS} = 0 V$			1	uA
		$V_{DS} = 48 V, V_{GS} = 0 V, T_J = 55^\circ C$			25	
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 V, V_{GS} = 10 V$	30			A
Drain-Source On-Resistance	$r_{DS(on)}$	$V_{GS} = 10 V, I_D = 15.2 A$			94	mΩ
		$V_{GS} = 4.5 V, I_D = 14 A$			109	
Forward Transconductance	g_{fs}	$V_{DS} = 15 V, I_D = 15.2 A$		20		S
Diode Forward Voltage	V_{SD}	$I_S = 21 A, V_{GS} = 0 V$		1.03		V
Dynamic						
Total Gate Charge	Q_g	$V_{DS} = 30 V, V_{GS} = 4.5 V,$ $I_D = 15.2 A$		5.1		nC
Gate-Source Charge	Q_{gs}			2.3		
Gate-Drain Charge	Q_{gd}			2.0		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 30 V, R_L = 2 \Omega,$ $I_D = 15.2 A,$ $V_{GEN} = 10 V, R_{GEN} = 6 \Omega$		4		ns
Rise Time	t_r			9		
Turn-Off Delay Time	$t_{d(off)}$			17		
Fall Time	t_f			19		
Input Capacitance	C_{iss}	$V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz$		475		pF
Output Capacitance	C_{oss}			59		
Reverse Transfer Capacitance	C_{rss}			36		

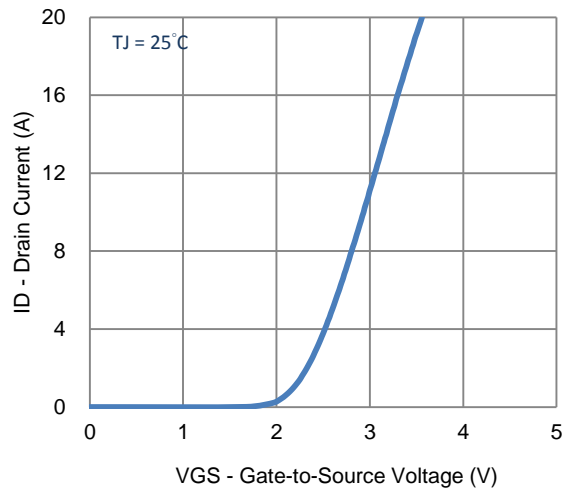
Notes

- Pulse test: $PW \leq 300 \mu s$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

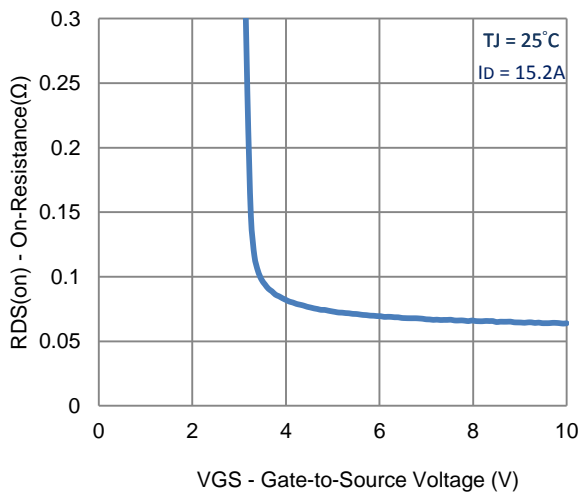
Typical Electrical Characteristics



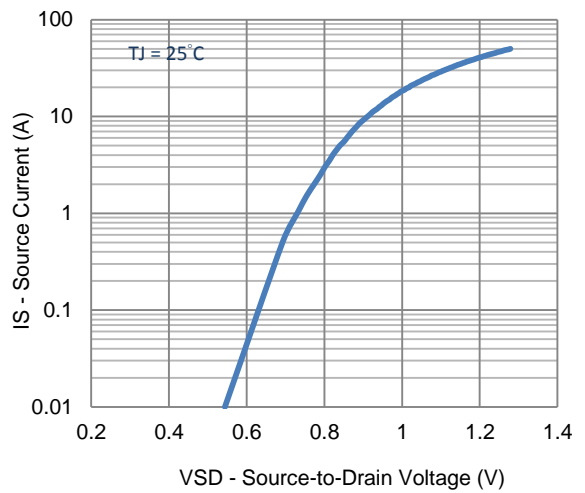
1. On-Resistance vs. Drain Current



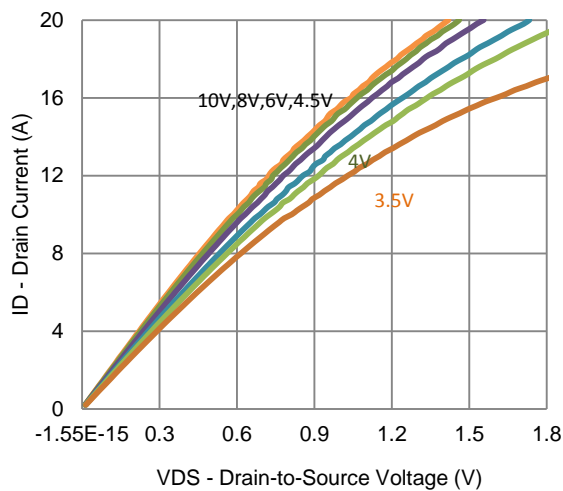
2. Transfer Characteristics



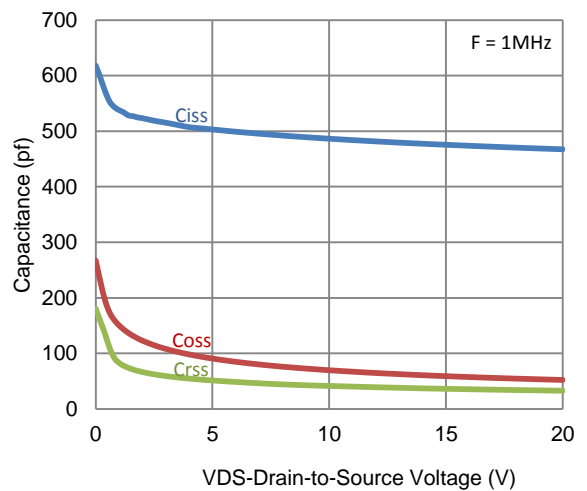
3. On-Resistance vs. Gate-to-Source Voltage



4. Drain-to-Source Forward Voltage

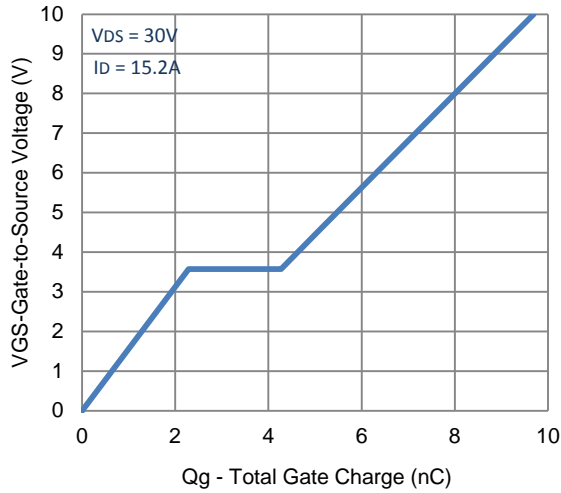


5. Output Characteristics

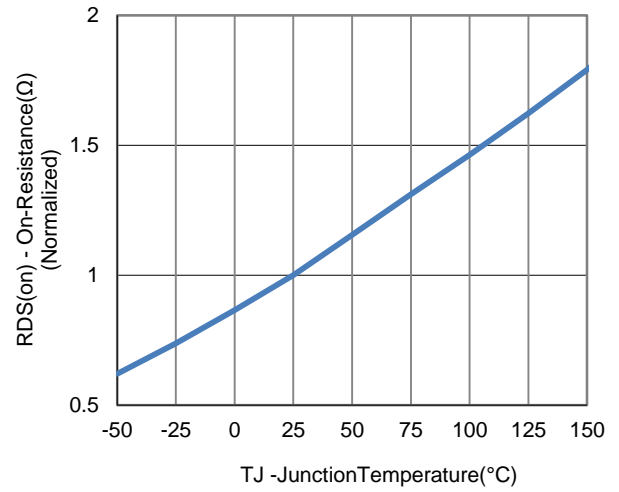


6. Capacitance

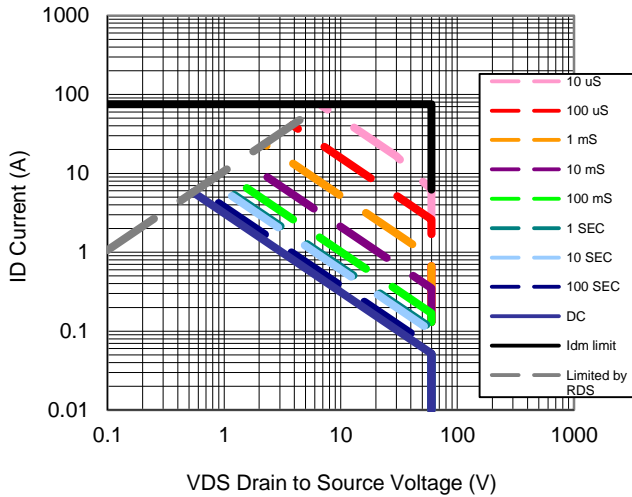
Typical Electrical Characteristics



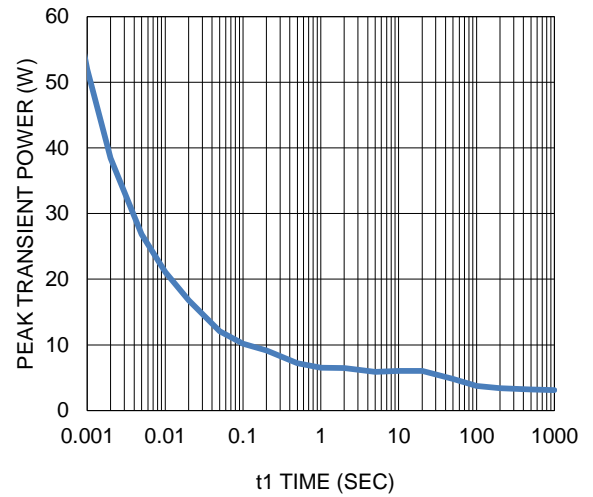
7. Gate Charge



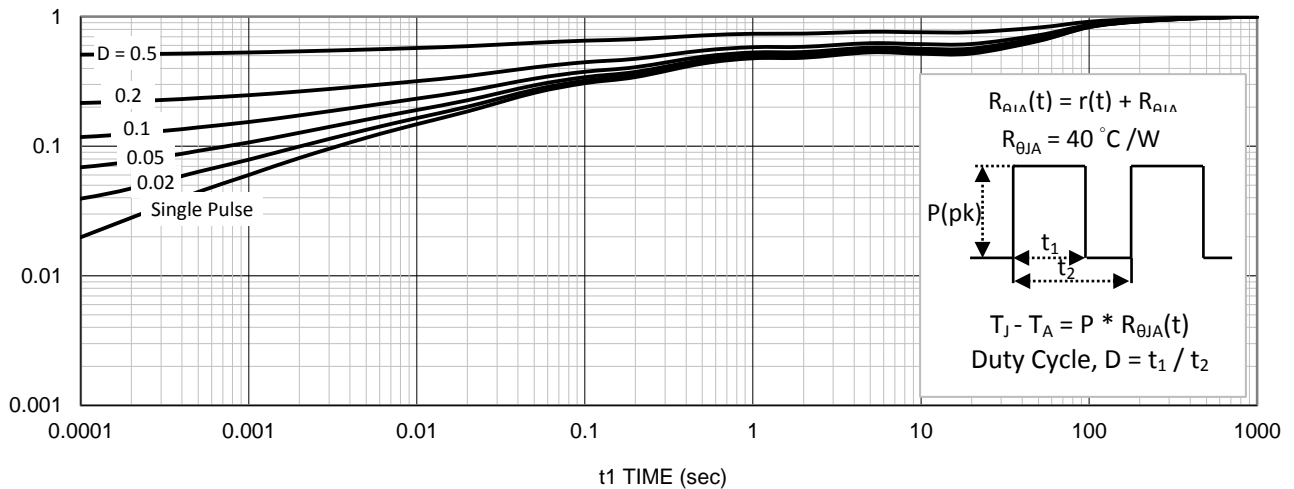
8. Normalized On-Resistance Vs Junction Temperature



9. Safe Operating Area



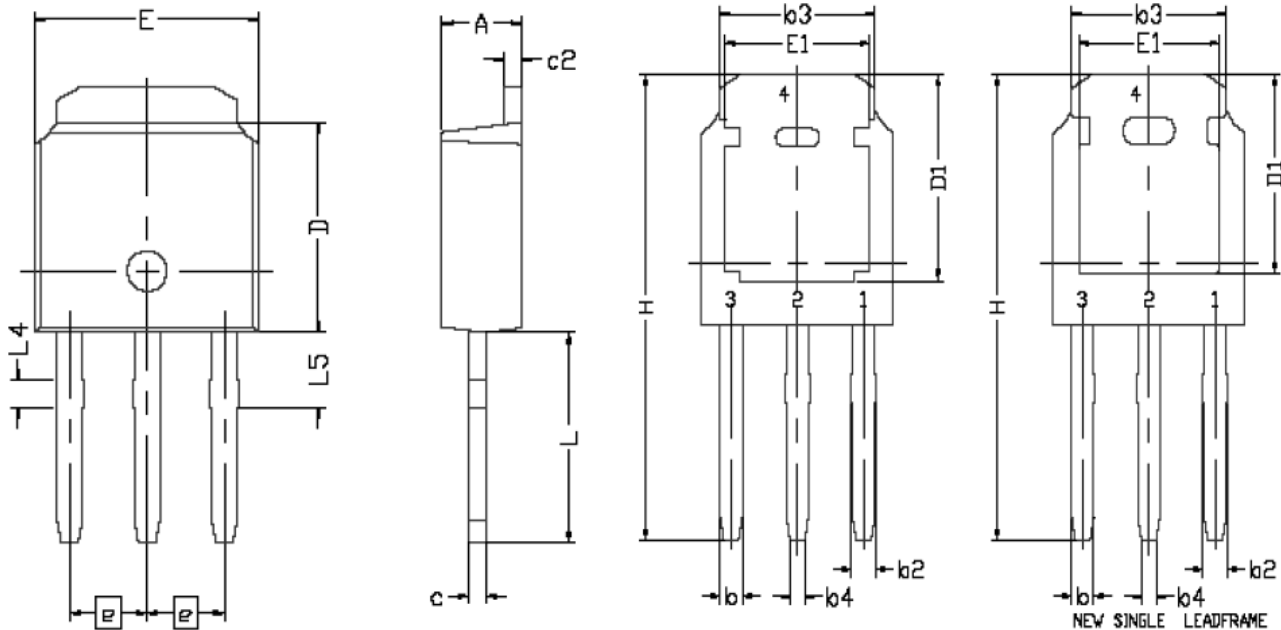
10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information

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SYMBOL	DIMENSIONAL REQMTS		
	MIN	NOM	MAX
E	6.40	6.60	6.731
L	5.88	6.08	6.28
L4	0.66	0.76	0.86
L5	1.96	2.16	2.36
D	6.00	6.10	6.223
H	12.90	13.20	13.50
b	0.64	0.76	0.88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
b4	0.41	0.51	0.61
e	2.286 BSC		
A	2.20	2.30	2.38
c	0.40	0.50	0.60
c2	0.40	0.50	0.60
D1	5.30	--	--
E1	4.40	--	--